

Supporting information

Cesium-lead-bromine Perovskites with Balanced Stoichiometry Enabled by Sodium-bromide Doping for All-Vacuum Deposited Silicon-based Light-emitting Diodes

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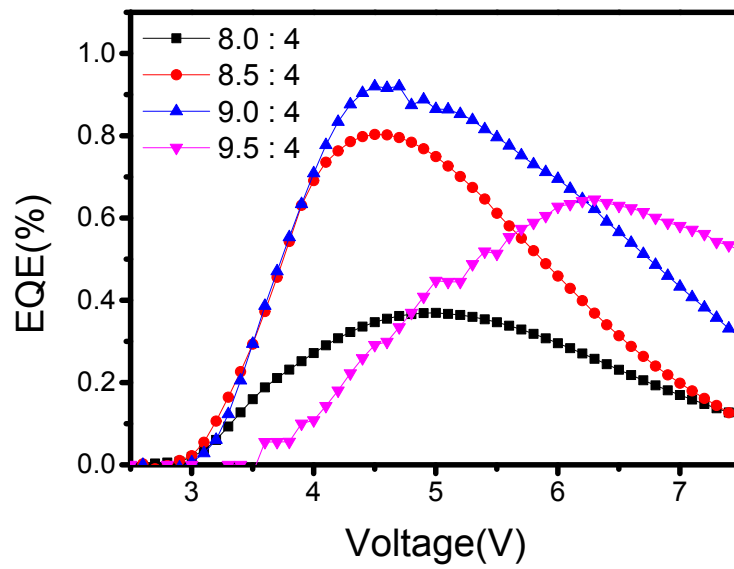


Figure S1. EQE of PeLED devices with different CsBr/PbBr₂ molar ratios under different working voltages

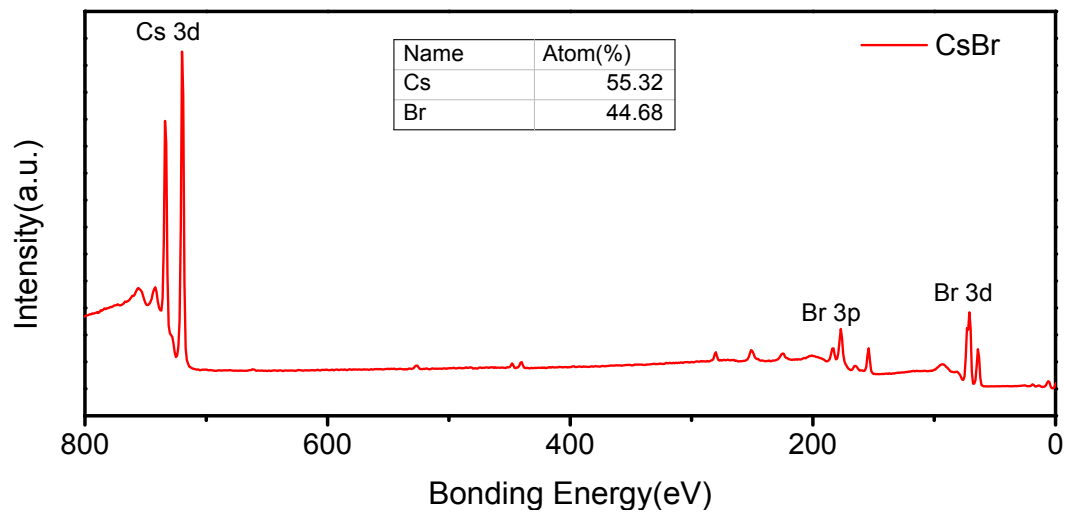


Figure S2. XPS full spectra of the CsBr film prepared by VVD method

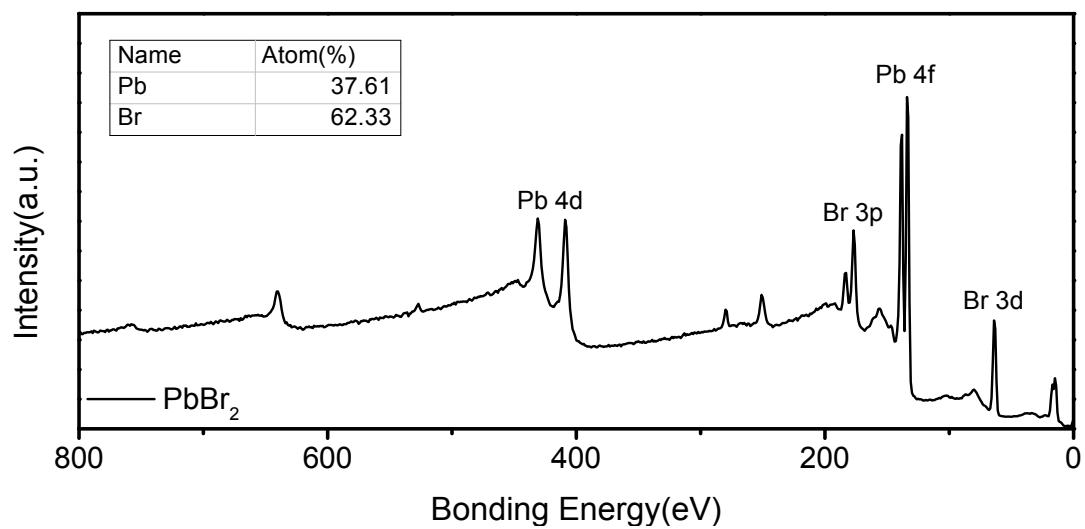


Figure S3. XPS full spectra of the PbBr₂ film prepared by VVD method

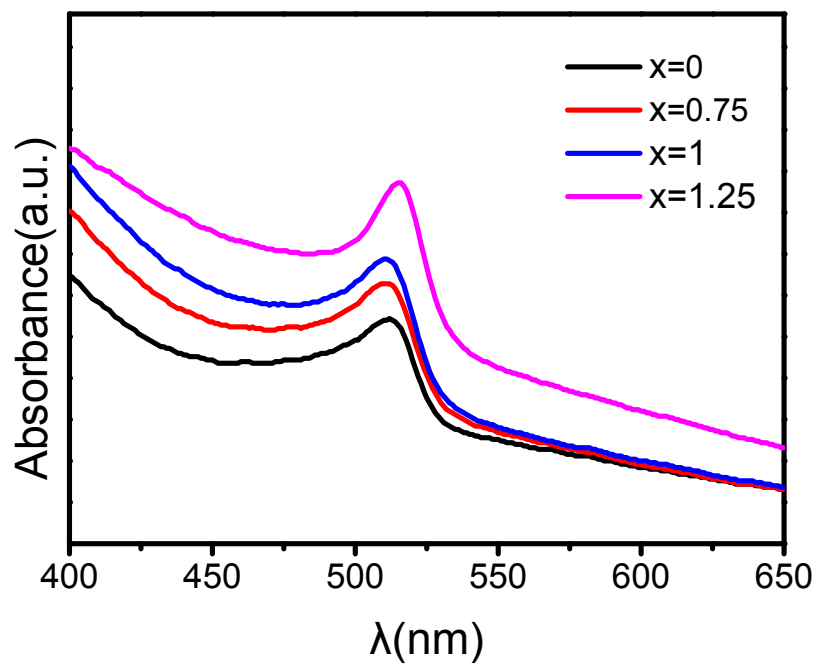


Figure S4. UV-vis absorbance spectra of films with different CsBr/PbBr₂/NaBr molar ratios

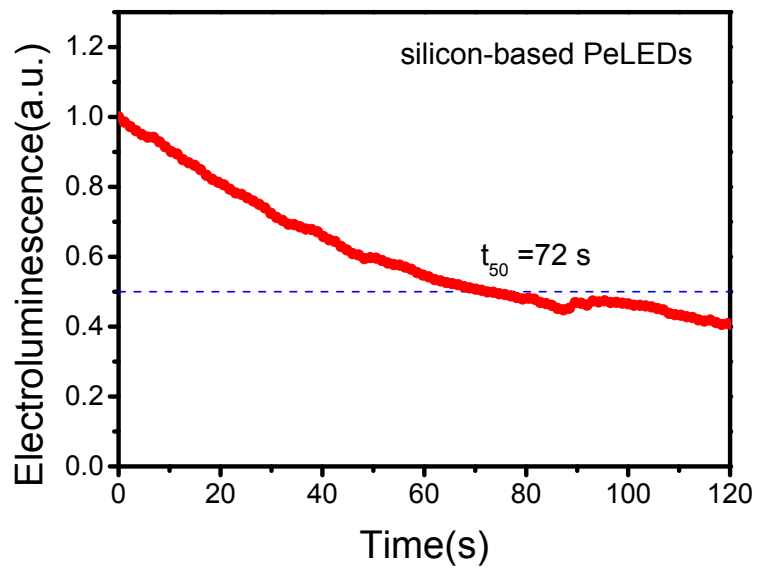


Figure S5. Electroluminescence intensity of silicon-based PeLEDs with NaBr doping as a function of operating time under constant biasing